L Number	Hits	Search Text	DB	Tim stamp
21	116	(acc leration nears ns r) and 257/415	USPAT;	2004/01/12
			US-PGPUB;	09:40
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
22	28	(acceleration near sensor).clm. and 257/415	USPAT;	2004/01/12
			US-PGPUB:	09:40
ì			EPO; JPO;	
İ			DERWENT;	
			IBM_TDB	
•	21157	acceleration adj sensor	USPAT;	2004/01/06
1		•	US-PGPUB;	11:12
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
. 1	2028	(acceleration adj sensor).clm.	USPAT;	2004/01/06
	<del></del>		US-PGPUB;	11:12
			EPO; JPO;	
1			DERWENT;	
Ì			IBM_TDB	
	177	(acceleration adj sensor).clm. and	USPAT;	2004/01/06
-		beam.clm.	US-PGPUB;	11:12
			EPO; JPO;	, <b>-</b>
			DERWENT;	
Ì			IBM_TDB	
_	5	(acceleration adj sensor).clm. and	USPAT;	2004/01/06
ĺ	_	beam.clm. and (piezoresistor).clm.	US-PGPUB;	11:13
		(1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-	EPO; JPO;	,
j			DERWENT;	
1	ı		IBM_TDB	
	0	(acceleration adj sensor).clm. and	USPAT;	2004/01/06
		beam.clm. and (piezoresistor).clm. and (tft	US-PGPUB;	11:13
		or (thin near film near transistor)).clm.	EPO; JPO;	
			DERWENT;	
ļ			IBM_TDB	
	0	(acceleration adj sensor).clm. and	USPAT;	2004/01/06
		(piezoresistor).clm. and (tft or (thin near	US-PGPUB;	11:13
		film near transistor)).clm.	EPO; JPO;	
į	i	,,	DERWENT;	
			IBM_TDB	
	0	(acceleration adj sensor).clm. and (tft or	USPAT;	2004/01/06
1		(thin near film near transistor)).clm.	US-PGPUB;	11:16
		<i>"</i>	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	1	(acceleration adj sensor).clm. and (tft or	USPAT;	2004/01/06
	_	(thin near film near transistor))	US-PGPUB;	11:17
			EPO; JPO;	.= ==================================
			DERWENT;	
			IBM_TDB	

·	26	(ac I rati n adj sensor) and (tft or (thin	USPAT;	2004/01/06
i		n ar film near transist r))	US-PGPUB;	11:17
	1	,,	EPO; JPO;	
	ļ		DERWENT;	
ļ	1		IBM_TDB	
_	3	(acceleration adj sensor) and (tft or (thin	USPAT;	2004/01/06
		near film near transistor)) and (piezo or	US-PGPUB;	11:17
)		piezoresistor)	EPO; JPO;	
	]	piezoresistory	DERWENT;	
]	1		IBM_TDB	
1	165494	sensor.clm.	USPAT;	2004/01/06
-	105494	sensor.cim.	US-PGPUB;	11:17
}	}		1	11:17
	1		EPO; JPO;	
ļ			DERWENT;	
			IBM_TDB	000 4/04/00
•	259	sensor.clm. and (tft or (thin near film near	USPAT;	2004/01/06
	1	transistor)).clm.	US-PGPUB;	11:18
[			EPO; JPO;	
1	1		DERWENT;	
	_		IBM_TDB	
-	0	sensor.clm. and (tft or (thin near film near	USPAT;	2004/01/06
	Ì	transistor)).clm. and piezoresistor.clm.	US-PGPUB;	11:19
1			EPO; JPO;	
	1		DERWENT;	
1	}		IBM_TDB	
-	0	(acceleration near sensor).clm. and (tft or	USPAT;	2004/01/06
ļ	,	(thin near film near transistor)).clm.	US-PGPUB;	11:20
			EPO; JPO;	
Į.			DERWENT;	
			IBM_TOB	
-	6870	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
1	1		US-PGPUB;	11:20
]			EPO; JPO;	
}			DERWENT;	
}			IBM_TDB	
-	259	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
}		and sensor.clm.	US-PGPUB;	11:21
}			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	26	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
ļ	1	and sensor.clm. and beam.clm.	US-PGPUB;	11:21
ł	1		EPO; JPO;	
	1		DERWENT;	
	1		IBM_TDB	
-	15	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
	1	and sensor.cim. and beam.cim. and	US-PGPUB;	11:22
		sensor.ab.	EPO; JPO;	
			DERWENT;	
L	1		IBM_TDB	

		(484 (41-in 61 4i4	HCDAT.	2004/04/06
-	9	(tft or (thin n ar film n ar transist r)).clm.	USPAT;	2004/01/06
		and sens r.clm. and beam.clm. and	US-PGPUB;	11:22
		s ns r.ab. and substrat .clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	9	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
		and sensor.clm. and beam.clm. and	US-PGPUB;	11:22
1		sensor.ab. and substrate.clm. and (tft or	EPO; JPO;	
1		(thin near film near transistor)).clm.	DERWENT;	
			IBM_TDB	
-	0	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
	1	and sensor.cim. and beam.cim. and	US-PGPUB;	11:22
		sensor.ab. and substrate.clm. and (tft or	EPO; JPO;	
		(thin near film near transistor)).ab.	DERWENT;	
			IBM_TDB	
-	0	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
-		and sensor.cim. and beam.cim. and	US-PGPUB;	11:23
		sensor.ab. and substrate.clm. and (piezo or	EPO; JPO;	
1		piezoelectric or piezoresistor)	DERWENT;	
			IBM_TDB	
-	0	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
		and sensor.clm. and beam.clm. and	US-PGPUB;	11:23
		sensor.ab. and substrate.clm. and (piezo or	EPO; JPO;	
		piezoelectric or piezoresistor).clm.	DERWENT;	
			IBM_TDB	
-	1	(tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06
		and sensor.clm. and sensor.ab. and	US-PGPUB;	11:23
		substrate.clm. and (piezo or piezoelectric	EPO; JPO;	
		or piezoresistor).clm.	DERWENT;	
	0000		IBM_TDB	
-	2099	(acceleration near sensor).clm.	USPAT;	2004/01/06
			US-PGPUB;	11:24
1			EPO; JPO;	
<b>{</b>			DERWENT;	
	0	(accoloration mean source) also and (44 and	IBM_TDB	2004/04/00
1 -	3	(acceleration near sensor).clm. and (tft or (thin near film near transistor)).clm.	USPAT;	2004/01/06 11:24
1		tum neat min neat transistor)).cim.	US-PGPUB;	
	1		EPO; JPO;	
1	1		DERWENT;	
	1	(acceleration near sensor).clm. and (tft or	USPAT;	2004/01/06
	•	(thin near film near transistor))	US-PGPUB;	11:24
1	1	( IIVAI IIIIII IIEAI LIAIISISLUI))	EPO; JPO;	1 1:67
!	}		DERWENT;	
	[		IBM_TDB	
_	201	(acceleration near sensor).clm. and (piezo	USPAT;	2004/01/06
		or piezoelectric or piezoresistor).clm.	US-PGPUB;	11:24
		production of probabilities in probabilities	EPO; JPO;	- 112-4
			DERWENT;	
I	1		IBM_TDB	1

•	201	(acc leration n ars ns r).clm. and (piez	USPAT;	2004/01/06
		or piez electric r piezoresistor).clm.	U -PGPUB;	11:27
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
<b> </b> -	31	(acceleration near sensor).clm. and (piezo	USPAT;	2004/01/06
		or piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:28
		(cantilever or beam).clm.	EPO; JPO;	
		,	DERWENT;	
			IBM_TDB	
} _	4	(acceleration near sensor).clm. and (piezo	USPAT;	2004/01/06
ł		or piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:28
		(cantilever or beam).clm. and (thin near	EPO; JPO;	
		film)	DERWENT;	
l			IBM_TDB	
_	4	(acceleration near sensor).clm. and (piezo	USPAT;	2004/01/06
		or piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:28
		(cantilever or beam).clm. and ((thin near	EPO; JPO;	
Į.		film) or tft)	DERWENT;	
[			IBM_TDB	
l <b>-</b>	1	(acceleration near sensor).clm. and (piezo	USPAT;	2004/01/06
İ		or piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:29
		(cantilever or beam).clm. and ((thin near	EPO; JPO;	
İ		film) or tft).clm.	DERWENT;	
			IBM_TDB	
-	0	(acceleration near sensor).clm. and (piezo	USPAT;	2004/01/06
		or piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:29
1		(cantilever or beam).clm. and (tft).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(acceleration near sensor).clm. and (piezo	USPAT;	2004/01/06
	•	or piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:29
		(cantilever or beam).clm. and (tft)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	4	(sensor).clm. and (piezo or piezoelectric or	USPAT;	2004/01/06
}		piezoresistor).clm. and (cantilever or	US-PGPUB;	11:32
		beam).cim. and (tft)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2099	(acceleration near sensor).clm.	USPAT;	2004/01/06
			US-PGPUB;	11:32
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
•	56	(acceleration near sensor).clm. and	USPAT;	2004/01/06
		(insulating or dielectric).clm. and	US-PGPUB;	11:33
}	}	substrate.clm.	EPO; JPO;	
	}		DERWENT;	
	L		IBM_TDB	<u></u>

Γ.	0	(accelerati n near sensor).clm. and	USPAT;	2004/01/06
		(insulating or dielectric).clm. and	US-PGPUB;	11:33
ļ		substrate.clm. and tft	EPO; JPO;	11.00
			DERWENT;	
			IBM_TDB	
1_	23	(acceleration near sensor).clm. and	USPAT;	2004/01/06
	20	(insulating or dielectric).clm. and	US-PGPUB;	11:33
		substrate.clm. and (tft or (thin near film))	EPO; JPO;	11.55
]		and the or thin hear min)	DERWENT;	
<b>\</b>			IBM_TDB	
	0	(acceleration near sensor).clm. and	USPAT;	2004/01/06
	_	(insulating or dielectric).clm. and	US-PGPUB;	11:34
		substrate.clm. and (tft or (thin near film	EPO; JPO;	
1		near transistor))	DERWENT;	
		,	IBM_TDB	
_	4380	(insulating or dielectric).clm. and	USPAT;	2004/01/06
		substrate.clm. and (cantilever or	US-PGPUB;	11:35
		beam).clm.	EPO; JPO;	
			DERWENT;	
:			IBM_TDB	
-	3	(insulating or dielectric).clm. and	USPAT;	2004/01/06
		substrate.clm. and (cantilever or	US-PGPUB,	11:35
		beam).clm. and piezoresistor.clm.\	EPO; JPO;	
	İ		DERWENT;	
			IBM_TDB	
-	3	(insulating or dielectric).clm. and	USPAT;	2004/01/06
		substrate.clm. and (cantilever or	US-PGPUB;	11:35
	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	beam).clm. and piezoresistor.clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(insulating or dielectric).clm. and	USPAT;	2004/01/06
		substrate.clm. and (cantilever or	US-PGPUB;	11:35
		beam).clm. and piezoresistor.clm. and	EPO; JPO;	
	1	(acceleration near sensor).clm.	DERWENT;	
			IBM_TDB	
-	0	(insulating or dielectric).clm. and	USPAT;	2004/01/06
		substrate.clm. and (cantilever or beam).clm. and (piezo or piezoelectric or	US-PGPUB;	11:36
	}	1	EPO; JPO;	
		piezoresistor).clm. and (acceleration near sensor).clm.	DERWENT;	
	31	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:36
		(acceleration near sensor).clm.	EPO; JPO;	11.50
		(account it and action from	DERWENT;	
			IBM_TDB	
_	21	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:39
		(acceleration near sensor).clm. and	EPO; JPO;	
		(acceleration near sensor).ab.	DERWENT;	
	1		IBM_TDB	

	13	(cantilev r r beam).clm. and (piezo r	USPAT;	2004/01/06
		piezoel ctric r pi zoresistor).clm. and	US-PGPUB;	11:39
		(acceleration near sens r).clm. and	EPO; JPO;	
		(acceleration near sensor).ab. and	DERWENT;	
		beam.cim.	IBM TDB	}
_	6	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:40
		(acceleration near sensor).clm. and	EPO; JPO;	
		(acceleration near sensor).ab. and	DERWENT;	
		beam.clm. and substrate.clm.	IBM TDB	
_	0	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:40
1		(acceleration near sensor).clm. and	EPO; JPO;	
		(acceleration near sensor).ab. and	DERWENT;	
		beam.clm. and substrate.clm. and	IBM_TDB	
1		(insulating or dielectric).clm.		
ļ <u>_</u>	1	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:42
		(acceleration near sensor).clm. and	EPO; JPO;	
		(acceleration near sensor).ab. and	DERWENT;	
		beam.clm. and substrate.clm. and (thin	IBM_TDB	
		near film).clm.		
	o	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
	-	piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:42
<b>[</b>	}	(acceleration near sensor).clm. and	EPO; JPO;	
ļ		(acceleration near sensor).ab. and	DERWENT;	
		beam.clm. and substrate.clm. and (thin	IBM_TDB	
		near film).clm. and (pcb or printed).clm.		
	0	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
6		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:42
1		(acceleration near sensor).clm. and	EPO; JPO;	
		(acceleration near sensor).ab. and	DERWENT;	
		beam.clm. and substrate.clm. and (pcb or	IBM_TDB	
		printed).clm.		
-	6	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:42
		(acceleration near sensor).clm. and	EPO; JPO;	
		(acceleration near sensor).ab. and	DERWENT;	
		beam.clm. and substrate.clm.	IBM_TDB	
-	4	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:43
1		(acceleration near sensor).clm. and	EPO; JPO;	
		(acceleration near sensor).ab. and	DERWENT;	
		beam.clm. and substrate.clm. and	IBM_TDB	
		(cantilever or cantilevered).clm.		
<b>  -</b>	4	(cantilever or beam).clm. and (piezo or	USPAT;	2004/01/06
		piezoelectric or piezoresistor).clm. and	US-PGPUB;	11:45
		(acceleration near sensor).clm. and	EPO; JPO;	ŀ
]		(acceleration near sensor).ab. and	DERWENT;	
		beam.cim. and substrate.cim. and	IBM_TDB	
		(cantilever or cantilevered).clm. and		
L		(cantil v r rcantilever d).ab.		